



Docket No.: GR 99 P 2591 P

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M. Allen

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By: [Signature]

Date: 5/11/01

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : Gerald Deboy et al.
Applic. No. : 09/838,743
Filed : April 19, 2001
Title : Vertically Structured Power Semiconductor Component

INFORMATION DISCLOSURE STATEMENT

Hon. Commissioner of Patents and Trademarks,
Washington, D.C. 20231

Sir:

In accordance with 37 C.F.R. 1.98 copies of the following patents and/or publications are submitted herewith:

German Published, Non-Prosecuted Application DE 197 31 495 A1 (Laska et al.), dated January 28, 1999, bipolar transistor controllable through field effect and method for its production;

European Application EP 0 061 551 A2 (Nakagawa et al.), dated October 6, 1982;

European Application EP 0 222 326 A2 (Yilmaz et al.), dated May 20, 1987;

European Application EP 0 503 605 A2 (Okabe et al.), dated September 16, 1992;

T. Laska et. al.: "A 2000 V-Non-Punch-Through-IGBT with Dynamical Properties like a 1000 V-IGBT", CH2865, 1990 IEEE, pp. 807-810, XP 000279629;

T. Laska et al.: "Ultrathin-Wafer Technology For A New 600V-NPT-IGBT", 0-7803-3993-2/97, IEEE, pp. 361-364, XP-000800221;

If no translation of pertinent portions of any foreign language patents or publications mentioned above is included with the aforementioned copies of those applications, patents and/or publications, it is because no existing translation is readily available to the applicant.

Respectfully submitted,



For Applicants

Mark P. Weichselbaum
Reg. No. 43,248

Date: 05/11/2001

Lerner And Greenberg, P.A.
Post Office Box 2480
Hollywood, FL 33022-2480
Tel: (954) 925-1100
Fax: (954) 925-1101

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